

ABSTRACT OF DISCLOSURE

A semiconductor device includes: a collector region of first conductive type formed on a semiconductor substrate; a base region of second conductive type formed on the collector region of first conductive type; a non-doped layer forming region formed in part of a surface region of the base region of second conductive type; an emitter region of first conductive type formed in the non-doped layer forming region so that a bottom of the emitter region reaches the base region of second conductive type; a base leading-out region of second conductive type formed on the base region of second conductive type; a dielectric formed on an upper portion and a side portion of the base leading-out region of second conductive type and the non-doped layer forming region; and an emitter leading-out region of first conductive type formed on the emitter region of first conductive type.